

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	379	lossy near3 layer	US-PGPUB; USPAT	OR	OFF	2006/06/16 10:36
L2	21	1 and "372"/\$.ccls.	US-PGPUB; USPAT	OR	OFF	2006/06/16 10:55
L3	1	gain near3 gaas and lossy near3 gaas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/16 10:56
S1	1	("5926494").PN.	US-PGPUB; USPAT	OR	OFF	2006/06/11 13:43
S2	7	((("5926494") or ("3786368") or ("3970960") or ("3992681") or ("4249141") or ("4757268") or ("5754572"))).PN.	US-PGPUB; USPAT	OR	OFF	2006/06/15 17:46
S3	5	("3786368"   "3970960"   "3992681"   "4757268"   "5754572").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/06/11 14:31
S4	194	372/50.1.ccls. and 372/46.01.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:11
S5	308	"372"/\$.ccls. and quantum near3 dot\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:41
S6	495	"372"/66.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:41
S7	427	"372"/68.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:41
S8	26	S6 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:42

## EAST Search History

S9	3	((plural\$3 or multiple) near3 gain near3 (medium or region\$1)) with lossy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:48
S10	5	("3786368"   "3970960"   "3992681"   "4757268"   "5754572").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/06/15 15:55
S11	32	((reduc\$5 near3 parasitic\$1) same (gain near3 medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 15:57
S12	191	thermally near3 conducting near3 substrate	US-PGPUB; USPAT	OR	OFF	2006/06/15 16:37
S13	14	S12 and "372"/\$.ccls.	US-PGPUB; USPAT	OR	OFF	2006/06/15 16:37
S14	0	((four near3 level near3 semiconductor) with gaas)	US-PGPUB; USPAT	OR	OFF	2006/06/15 17:47
S15	2	((four near3 level with semiconductor) with gaas)	US-PGPUB; USPAT	OR	OFF	2006/06/15 17:48
S16	2	((four near3 level with semiconductor) with gaas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 17:48
S17	3	((four near3 level with semiconductor) same gaas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 17:49
S18	10	((four near3 level) same gaas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 17:50
S19	2	((four near3 level) with gaas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 17:49
S20	15	((four or three) near3 level) with gaas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/06/15 17:51